

FS70SM-06

High-Speed Switching Use Nch Power MOS FET

REJ03G1430-0200

(Previous: MEJ02G0099-0101)

Rev.2.00 Aug 07, 2006

Features

• Drive voltage: 10 V

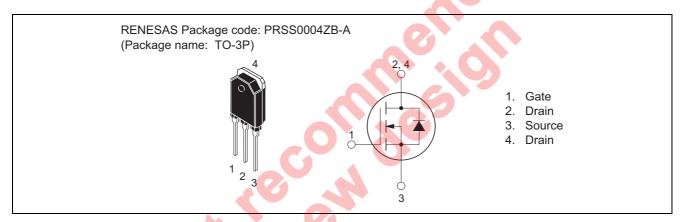
V_{DSS}: 60 V

• $r_{DS(ON) (max)}$: 7.5 m Ω

• I_D: 70 A

• Integrated Fast Recovery Diode (TYP.): 85 ns

Outline



Applications

Motor control, Lamp control, Solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

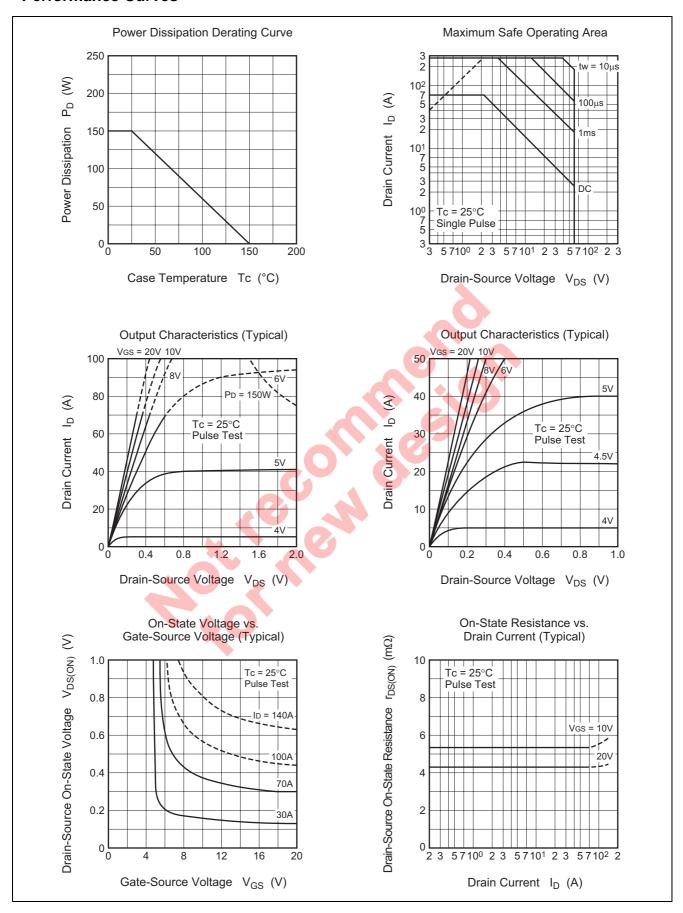
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	60	V	$V_{GS} = 0 V$
Gate-source voltage	V_{GSS}	±20	V	$V_{DS} = 0 V$
Drain current	I _D	70	Α	
Drain current (Pulsed)	I _{DM}	280	Α	
Avalanche drain current (Pulsed)	I _{DA}	70	Α	L = 100 μH
Source current	Is	70	Α	
Source current (Pulsed)	I _{SM}	280	Α	
Maximum power dissipation	P _D	150	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	4.8	g	Typical value

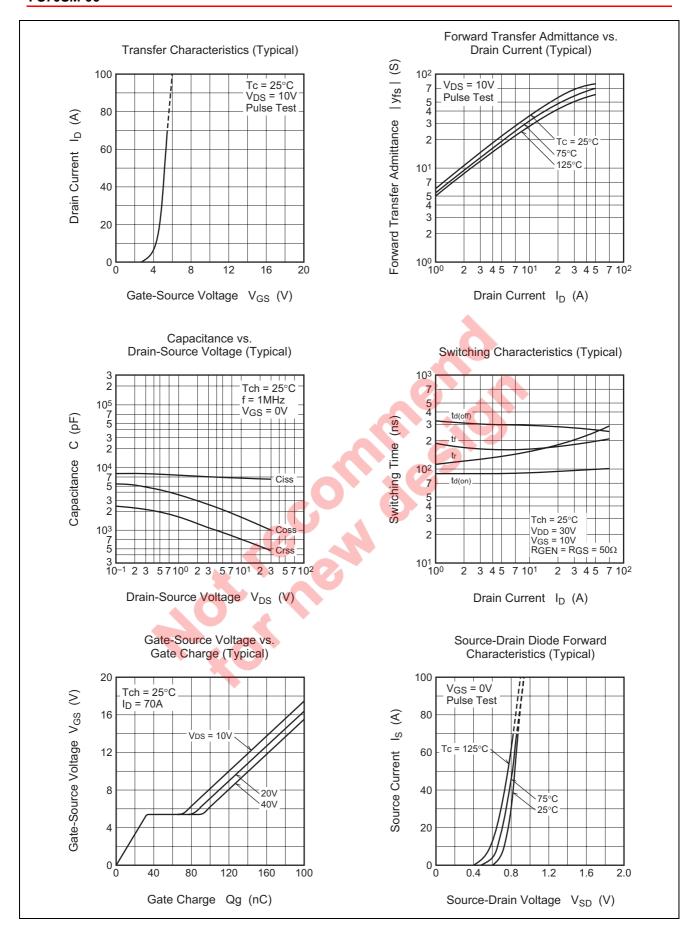
Electrical Characteristics

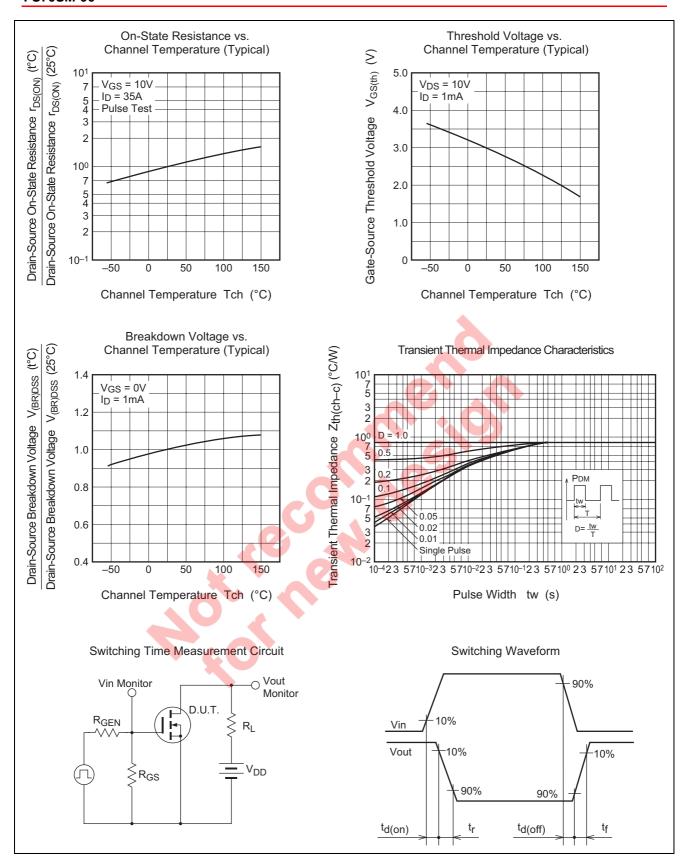
 $(Tch = 25^{\circ}C)$

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain-source breakdown voltage	V _{(BR)DSS}	60	—	_	V	I _D = 1 mA, V _{GS} = 0 V
Gate-source leakage current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I _{DSS}	_	_	0.1	mA	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	V _{GS(th)}	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	5.7	7.5	mΩ	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}$
Drain-source on-state voltage	V _{DS(ON)}	_	0.200	0.263	V	I _D = 35 A, V _{GS} = 10 V
Forward transfer admittance	y _{fs}	50	70	_	S	I _D = 35 A, V _{DS} = 10 V
Input capacitance	Ciss	_	6540	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	1640	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	790	_	pF	
Turn-on delay time	t _{d(on)}	_	95	_	ns	$V_{DD} = 30 \text{ V}, I_D = 35 \text{ A},$
Rise time	t _r	_	195	_	ns	V _{GS} = 10 V,
Turn-off delay time	t _{d(off)}	_	290	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t _f	_	210	_	ns	
Source-drain voltage	V_{SD}	_	1.0	1.5	V	I _S = 35 A, V _{GS} = 0 V
Thermal resistance	R _{th(ch-c)}	_	_	0.83	°C/W	Channel to case
Reverse recovery time	t _{rr}	_	85		ns	$I_S = 70 \text{ A}, d_{is}/d_t = -100 \text{ A/}\mu\text{s}$
		_				
		0	4	0		

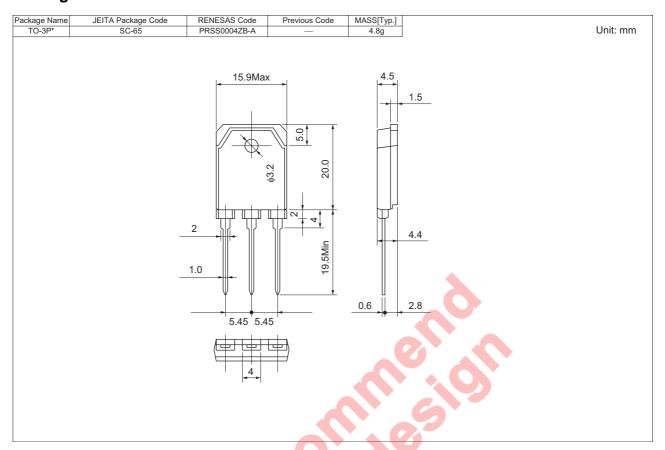
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Static electricity prevention bag	20	Type name	FS70SM-06
Lead form	Plastic Magazine (Tube)	30	Type name – Lead forming code	FS70SM-06-A8

Note: Please confirm the specification about the shipping in detail.

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